



TECHNICAL SPECIFICATION



Nanomanufacturing – Key control characteristics – Part 6-14: Graphene-based material – Defect level: Raman spectroscopy

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

NANOMANUFACTURING – KEY CONTROL CHARACTERISTICS –

Part 6-14: Graphene-based material – Defect level: Raman spectroscopy

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- the subject is still under technical development or where, for any other reason, there is the future but no immediate possibility of an agreement on an International Standard.

Technical Specifications are subject to review within three years of publication to decide whether they can be transformed into International Standards.

IEC TS 62607-6-14, which is a Technical Specification, has been prepared by IEC technical committee 113: Nanotechnology for electrotechnical products and systems.

The text of this Technical Specification is based on the following documents:

Enquiry draft	Report on voting
113/495/DTS	113/536/RVDTS

Full information on the voting for the approval of this Technical Specification can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts of the IEC TS 62607 series, published under the general title *Nanomanufacturing – Key control characteristics*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under "<http://webstore.iec.ch>" in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

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INTRODUCTION

Graphene has been intensively studied by researchers from both academic and industrial communities due to its unique properties, which include exceptional thermal conductivity, great strength and excellent transparency. Defects in graphene influence its optical and magnetic performance, electronic structure and thermal conductivity, thus influencing its applications. Therefore, defect is a key control characteristic for the fabrication of high-quality graphene for desired applications.

One of the most useful methods to evaluate defect level in graphene is Raman spectroscopy, which is sensitive to the structure of samples. This method is efficient, non-contact and well-understood. The defect states and boundary states of realistic graphene material will induce a series of Raman scattering processes (Figure 1). Some of scattering processes are only associated with defective states, which are used in this document to analyse defect level in graphene powder.

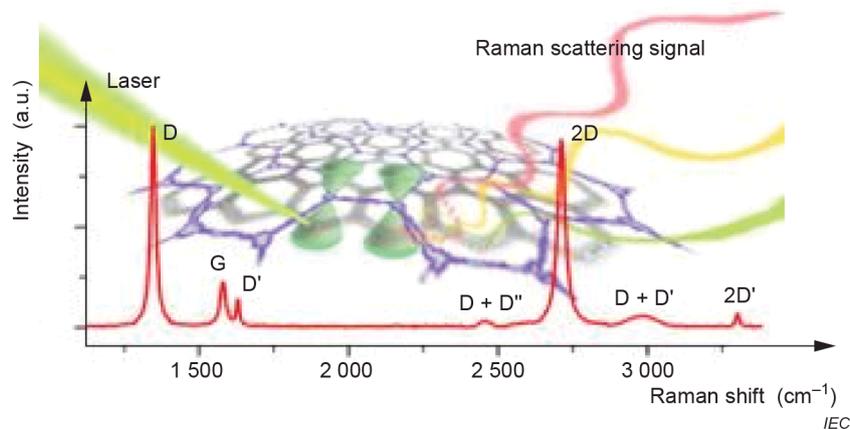


Figure 1 – Schematic diagram of Raman scattering processes in realistic graphene material

Commercialized graphene samples can be classified by their physical forms as graphene film, graphene powder and graphene solution. Figure 2 shows the schematic packing configurations of graphene flakes in graphene film (left side of Figure 2) and graphene powder (right side of Figure 2) and their corresponding SEM images.

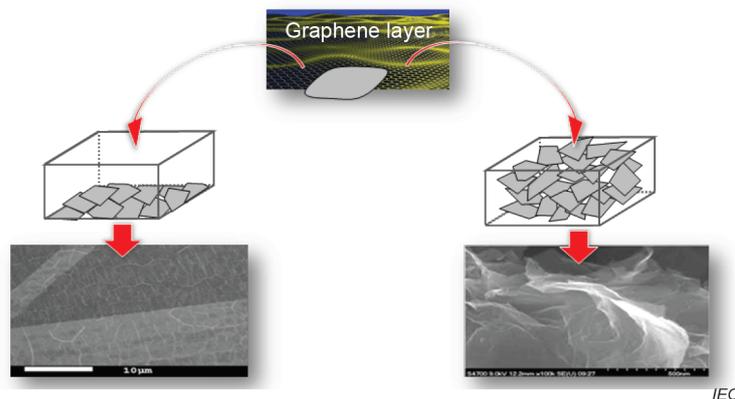


Figure 2 – Different packing configurations of graphene flakes in film (left) and powder (right)

Usually, defects in graphene films are characterized by the intensity ratio of two principle bands – D band and G band – in Raman spectra (symbolized by I_D/I_G) [1],[2]. However, in graphene powders consisting of flakes with sizes below 10 μm there are numerous edges and boundary states, which all contribute to the D-band signal and make its correlation to various defects problematic. The D-band intensity could result from the contribution of edges, boundary states or defects, so it is not appropriate to determine the defect level of graphene powder with the parameter I_D/I_G .

D+D' band is only relevant with defects in graphene powder, but not with edges and boundary states. Therefore, in order to characterize defect level in graphene powder, the intensity ratio of D+D' and 2D bands (symbolized by $I_{D+D'}/I_{2D}$) is proposed as a more relevant parameter in this document. Detailed information can be found in Annex D.

NANOMANUFACTURING – KEY CONTROL CHARACTERISTICS –

Part 6-14: Graphene-based material – Defect level: Raman spectroscopy

1 Scope

This part of IEC TS 62607 establishes a standardized method to determine the structural key control characteristic

- defect level
for powders consisting of graphene-based material by

- Raman spectroscopy.

The defect level is derived by the intensity ratio of the D+D' band and 2D band in Raman spectrum, $I_{D+D'}/I_{2D}$.

- The defect level determined in accordance with this document will be listed as a key control characteristic in the blank detail specification for graphene IEC 62565-3-1 for graphene powder.
- The method is applicable for graphene powder or graphene-based material, e.g. reduced graphene oxide (rGO), bilayer graphene, trilayer graphene and few-layer graphene.
- Typical application areas are quality control and classification for graphene manufacturers, and product selection for downstream users.
- The method described in this document is appropriate if the physical form of graphene is powder.

2 Normative references

There are no normative references in this document.